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ISM200, 300, 400, 500: Hybrid Optocouplers

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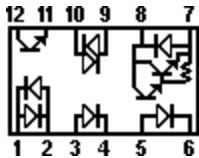
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Circuit and Package

Example Circuit, ISM400 (different custom options are available):



Measurement Units: mm	ISM200	ISM300	ISM400	ISM500

		8 pin	12 pin	16 pin	20 pin
	d	2.54			
	l	8.89	13.97	19.05	24.13
	s	7.52			

Description

The ISM200, ISM300, ISM400, ISM500 series are optically coupled isolators, consisting of a multichannel of different optocoupler circuits. Each channel can be designed to meet different configurations of the pin-outs to meet customer needs. The circuits consist of Gallium Arsenide infrared emitting diodes and a selection of NPN silicon phototransistor, phototriac, photodarlington, photodiode and integrated circuits mounted in a dual-in-line package. The company can offer a surface mount version package. (For surface mount requirement, add suffix S.)

Applications

Telecommunications, Modem, Data Systems, Switch Mode Power Supplies, Telephone Systems.

Absolute Maximum Ratings (Ta=25°C)

Storage Temperature:	-40°C to +125°C
Operating Temperature:	-30°C to +100°C
Lead Soldering:	260°C for 10s, 1.6mm from case
Input-to-Output Insulation Test Voltage:	±2500Vrms (Transient Overvoltage, t=10s)

Input Diode

Forward DC Current:	50mA
Reverse DC Voltage:	3V
Peak Forward Current:	1A (pw.=100µs, duty ratio 0.001)
Power Dissipation:	70mW
Derate Linearly:	1.33mW/°C above 25°C

Output

Collector-Emitter Voltage BV_{ce0} :	35V
Emitter-Base Voltage BV_{e0} :	6V
Collector Current:	50mA
Power Dissipation:	150mW
Derate Linearly:	2.00mW/°C above 25°C

Electrical Characteristics

Phototransistor Option

INPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F=50mA$			1.5	V
I_R	Reverse Current	$V_R=3V$			10	μA
C_T	Capacitance	$f=1MHz, V_R=0$				pF
OUTPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{CEO}	Collector-Emitter Voltage	$I_C=1mA$	30	50		V
BV_{ECO}	Emitter-Collector Voltage	$I_E=0.1mA$	7	8		V
I_{CEO}	Collector-Emitter Dark Current	$V_{CE}=10V$			50	nA
C_{CE}	Collector-Emitter Capacitance	$V_{CE}=10V, f=1MHz$				pF
COUPLED	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_C / I_F	DC Current Transfer Ratio	$I_F=10mA, V_{CE}=10V$	20	50		%
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_F=16mA, I_C=1.6mA$		0.2	0.5	V
C_F	Floating Capacitance	$V=0, f=1MHz$		0.6	1	pF
R_{ISO}	Input-to-Output Isolation Resistance	$V_{IO}=500V$	50			Gohm

High Collector/Emitter Voltage Transistor Option

INPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = \pm 20\text{mA}$		1.2	1.4	V
I_R	Reverse Current	$V_R = 3\text{V}$			10	μA
C_T	Terminal Capacitance	$f = 1\text{MHz}, V = 0$		30	250	pF
OUTPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{CEO}	Collector-Emitter Voltage	$I_C = 1\text{mA}$	30	50		V
BV_{ECO}	Emitter-Collector Voltage	$I_E = 0.1\text{mA}$	7	8		V
I_{CEO}	Collector-Emitter Dark Current	$V_{CE} = 20\text{V}, I_F = 0$			100	nA
COUPLED	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_C/I_F	DC Current Transfer Ratio	$I_F = \pm 5\text{mA}, V_{CE} = 5\text{V}$	20	50	300	%
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_F = \pm 20\text{mA}, I_C = 1\text{mA}$		0.1	0.2	V
C_F	Floating Capacitance	$V = 0, f = 1\text{MHz}$		0.6	1.0	pF
R_{ISO}	Input-to-Output Isolation Resistance	$V_{IO} = 500\text{V}$	50	100		Gohm
T_{ON}	Turn-On Time	$V_{CE} = 2\text{V}, I_C = 2\text{mA}, R_L = 100\text{ohm}$		4	18	μs
T_{OFF}	Turn-Off Time			3	18	μs

AC Input Option

INPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = \pm 20\text{mA}$		1.2	1.4	V
I_R	Reverse Current	$V_R = 4\text{V}$			10	μA
C_T	Terminal Capacitance	$f = 1\text{kHz}, V = 0$		30	250	pF
OUTPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT

BV_{CEO}	Collector-Emitter Voltage	$I_C=1mA$	30	50		V
BV_{ECO}	Emitter-Collector Voltage	$I_E=0.1mA$	7	8		V
I_{CEO}	Collector-Emitter Dark Current	$V_{CE}=20V, I_F=0$			100	nA
COUPLED	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_C/I_F	DC Current Transfer Ratio	$I_F=\pm 1mA, V_{CE}=5V$	20			%
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_F=\pm 20mA, I_C=1mA$		0.1	0.2	V
C_F	Floating Capacitance	$V=0, f=1MHz$		0.6	1.0	pF
R_{ISO}	Input-to-Output Isolation Resistance	$V_{IO}=500V, RH=40\sim 60\%$	50	100		Gohm
T_{ON}	Turn-On Time	$V_{CE}=2V, I_C=2mA, R_L=100ohm$		4	18	μs
T_{OFF}	Turn-Off Time			3	18	μs

High Sensitivity Photodarlington Option

INPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F=10mA$		1.2	1.4	V
V_{FM}	Peak Forward Voltage	$I_{FM}=0.5A$			3	V
I_R	Reverse Current	$V_R=4V$			10	μA
C_T	Terminal Capacitance	$f=1kHz, V=0$		30	250	pF
OUTPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_{CEO}	Collector-Emitter Dark Current	$V_{CE}=200V, I_F=0, R_{BE}=\text{infinite}$			1	μA
COUPLED	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_C/I_F	DC Current Transfer Ratio	$I_F=1mA, V_{CE}=2V, R_{BE}=\text{infinite}$	1000			%
R_{IO}	Input-to-Output Isolation Resistance	$V_{IO}=500V, (\text{note } 1)$				Gohm

$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_F=20mA, I_C=100mA, R_{BE}=\text{infinite}$			0.5	V
C_F	Floating Capacitance	$V=0, f=1MHz$		0.6	1.0	pF
R_{ISO}	Input-Output Isolation Resistance	$V_{IO}=500V, RH=40\sim 60\%$	50	100		Gohm
T_{ON}	Turn-On Time	$V_{CE}=2V, I_C=20mA, R_L=100ohm, R_{BE}=\text{infinite}$		100	300	μs
T_{OFF}	Turn-Off Time			20	100	μs

Triac Output Circuit Option

INPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F=20mA$		1.2	1.4	V
I_R	Reverse Current	$V_R=3V$			10	μA
OUTPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_{DRM}	Repetitive Peak Off-State Current	$V_{DRM}=\text{Rated}$			1	μA
V_T	On-State Voltage	$I_T=100mA$		1.7	2.5	V
I_H	Holding Current	$V_D=6V$	0.1	1	3.5	mA
dV/dt	Critical Rate of Rise of Off-State Voltage	$V_{DRM}=\text{sqrt}(1/2) \text{ Rated}$	600			V/ μs
COUPLED	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
C_F	Floating Capacitance	$V=0, f=1MHz$		0.6	1	pF
R_{ISO}	Input-Output Isolation Resistance	$V_{IO}=500V, RH=40\sim 60\%$	50	100		Gohm
I_{FT}	Minimum Trigger Current	$V_D=6V, R_L=100ohm$			10	mA

Notes 1. Measured with input leads shorted together and output leads shorted together.

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